

Number	Hits	Search Text	DB	Time stamp
3	10	((("5989623") or ("6017820") or ("5723387")) or ("6110611") or ("6153524") or ("6146135") or ("5672239") or ("5672239") or ("5855726")).PN.	USPAT; EPO; JPO	2002/06/04 09:21
-	5939	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))	USPAT; EPO; JPO	2002/06/01 20:23
-	525	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and (156/345.\$ccls. 451/\$ccls. 216/\$ccls.)	USPAT; EPO; JPO	2002/06/01 18:48
-	375	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and (156/345.\$ccls. 451/\$ccls. 216/\$ccls.) and (wash\$3 rins\$3 clean\$3 dip\$3, 118/119.\$ccls.	USPAT; EPO; JPO	2002/06/01 20:23
-	1949	(118/119.\$CCLS.	USPAT; EPO; JPO	2002/06/01 18:53
-	94	(156/345.31).CCLS.	USPAT; EPO; JPO	2002/06/01 18:54
-	105	(156/345.12).CCLS.	USPAT; EPO; JPO	2002/06/01 18:54
-	59	(156/345.32).CCLS.	USPAT; EPO; JPO	2002/06/01 18:54
-	255	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate);and (156/345.\$ccls. 451/\$ccls. 216/\$ccls.) and (wash\$3 rins\$3 clean\$3 dip\$3) and dry\$3	USPAT; EPO; JPO	2002/06/01 20:34
-	483	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and (1011081/\$ipc.) and (wash\$3 rins\$3 clean\$3 dip\$3) and dry\$3	USPAT; EPO; JPO	2002/06/01 20:32
-	46	((etch\$3 and strip\$4 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and (118/345.\$ccls. and wash\$3 rins\$3 clean\$3 dip\$3)	USPAT; EPO; JPO	2002/06/01 20:30
-	8	((etch\$3 and strip\$4 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and (118/345.\$ccls. and wash\$3 rins\$3 clean\$3 dip\$3	USPAT; EPO; JPO	2002/06/01 20:31
-	1	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and (wash\$3 rins\$3 clean\$3 dip\$3) and dry\$3	USPAT; EPO; JPO	2002/06/01 20:33
-	40	((etch\$3 and strip\$4 and deposit\$3 and (polish\$3 "CMP" "chemical mechanical polishing" "chemical mechanical planarizing"))) and (semiconductor substrate))and ("cluster tool" and (wash\$3 rins\$3 clean\$3 dip\$3) and dry\$3 "applied materials").pn.	USPAT; EPO; JPO	2002/06/01 20:35

-	128	"applied materials".as. and (cluster adj tool)	USPAT;	2002/06/03 08:34
-	1	("6110011").PN.	EPO; JPO	
-			USPAT;	2002/06/03 10:44
-	2	("6017820") or ("6110011").PN.	EPO; JPO	
-			USPAT;	2002/06/03 10:44
-	3	"IPA vapor drier"	EPO; JPO	
-			USPAT;	2002/06/03 10:49
-	50228	electroplat\$3 electrodeposit\$3	EPO; JPO	
-		electropolish\$3	USPAT;	2002/06/03 10:51
-	17683	(electroplat\$3 electrodeposit\$3	EPO; JPO	
-		electropolish\$3) and copper	USPAT;	2002/06/03 10:51
-	7961	((electroplat\$3 electrodeposit\$3	EPO; JPO	
-		electropolish\$3) and copper) and insulat\$3	USPAT;	2002/06/03 10:52
-	33	((electroplat\$3 electrodeposit\$3	EPO; JPO	
-		electropolish\$3) and copper) and	USPAT;	2002/06/03 11:16
-		insulat\$3) and (cluster adj tool)	EPO; JPO	
-	1	("5989623").PN.	USPAT;	2002/06/03 11:16
-			EPO; JPO	
-	14280	dry\$3 with inert	USPAT;	2002/06/03 11:20
-			EPO; JPO	
-	344	(dry\$3 with inert) and (dry\$3 with	USPAT;	2002/06/03 11:21
-		plurality)	EPO; JPO	
-	1	((dry\$3 with inert) and (dry\$3 with	USPAT;	2002/06/03 11:21
-		plurality) and (cluster adj tool)	EPO; JPO	
-	129	drier with inert	USPAT;	2002/06/03 11:21
-			EPO; JPO	
-	4	(drier with inert) and (dry\$3 with	USPAT;	2002/06/03 11:24
-		plurality)	EPO; JPO	
-	56	(drier with inert) and (etch\$3 deposit\$3	USPAT;	2002/06/03 12:31
-		clean\$3)	EPO; JPO	
-	208402	(conduct\$3 copper) with (insulat\$3)	USPAT;	2002/06/03 12:37
-			EPO; JPO	
-	17108	((conduct\$3 copper) with (insulat\$3) and	USPAT;	2002/06/03 12:35
-		(vapor adj deposit\$3)	EPO; JPO	
-	454	(conduct\$3 copper) with (insulat\$3) and	USPAT;	2002/06/03 12:37
-		156/345\$.cols.	EPO; JPO	
-	23655	(copper) with (insulat\$3)	USPAT;	2002/06/03 12:37
-			EPO; JPO	
-	64	(copper) with (insulat\$3) and	USPAT;	2002/06/03 15:03
-		156/345\$.cols.	EPO; JPO	
-	2	((copper) with (insulat\$3) and	USPAT;	2002/06/03 12:42
-		156/345\$.cols. and (cluster adj tool)	EPO; JPO	
-	29	((copper) with (insulat\$3) and (cluster	USPAT;	2002/06/03 12:42
-		adj tool)	EPO; JPO	
-	1412	((copper) with (insulat\$3) and	EPO; JPO;	2002/06/03 15:04
-		h011021/\$.ipc.	DERWENT	
-	143	((copper) with (insulat\$3) and	EPO; JPO;	2002/06/03 15:04
-		h011021/\$.ipc. and polish\$3 "CMP"	DERWENT	
-		"chemical mechanical polishing" "chemical		
-		mechanical planarizing" planariz\$3.		
-	3	((copper) with (insulat\$3) and	EPO; JPO;	2002/06/03 15:18
-		h011021/\$.ipc. and h,02	DERWENT	